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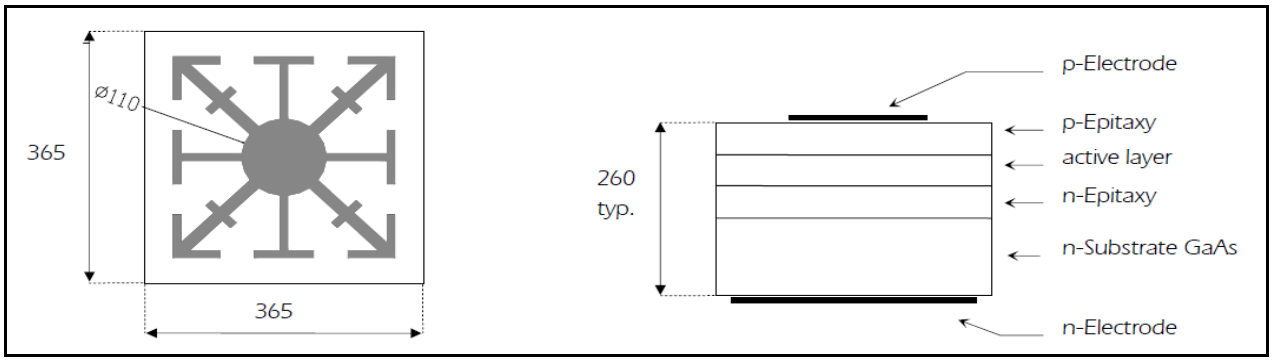
Data Sheet Preliminary

LED Chip Infrared EOLC-1140-17

Rev. 01, 2017

Radiation	Type	Electrodes
Infrared	InGaAs/GaAs, MQW	P (anode) up



Chip thickness: typ. 260±30 µm, bonding pad Ø110±15 µm, electrodes / metallization - Au alloy

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=20 mA	V_F		1.1	1.3	V
Forward voltage	I_F=100 mA	V_F		1.2	1.4	V
Reverse current	V_R=5 V	I_R			10	µA
Radiant power*	I_F=50 mA	Φ_e	2.5	3.5		mW
Radiant intensity*	I_F=100 mA	Φ_e	0.7	1		mW/sr
Peak wavelength	I_F=100 mA	λ_p	1120	1140	1160	nm
FWHM	I_F=20 mA	$\Delta\lambda_{0.5}$		70		nm
Switching time	I_F=100 mA	t_r, t_f		20		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. xxx xxx

RoHS COMPLIANT Pb-Free